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GaAs MMIC SPDT SWITCH, DC - 3 GHz

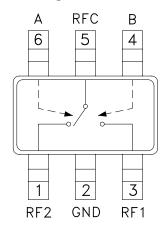


Typical Applications

The HMC545A / HMC545AE is ideal for:

- Cellular/3G Infrastructure
- Private Mobile Radio Handsets
- WLAN, WiMAX & WiBro
- Automotive Telematics
- Test Equipment

Functional Diagram



Features

Low Insertion Loss: 0.27 dB

High Input IP3: +54 dBm

Low DC Power Consumption

Positive Control: 0/+3V to 0/+8V

Ultra Small Package: SOT26

General Description

The HMC545A and HMC545AE are low-cost SPDT switches in 6-lead SOT26 plastic packages for use in general switching applications which require very low insertion loss and very small size. With 0.25 dB typical loss, these devices can control signals from DC to 3.0 GHz and are especially suited for IF and RF applications including Cellular/3G, ISM, automotive and portables. The design provides exceptional insertion loss performance, ideal for filter and receiver switching. RF1 and RF2 are reflective shorts when "Off". The two control voltages require a minimal amount of DC current and offer compatibility with CMOS and some TTL logic families.

Electrical Specifications

 $T_A = +25^{\circ}$ C, VctI = 0/+5 Vdc (Unless Otherwise Stated), 50 Ohm System

Parameter		Frequency	Min.	Тур.	Max.	Units
Insertion Loss		DC - 1.0 GHz DC - 2.5 GHz DC - 3.0 GHz		0.27 0.3 0.4	0.4 0.5 0.7	dB dB dB
Isolation		DC - 2.0 GHz DC - 2.5 GHz DC - 3.0 GHz	26 22 19	31 26 22		dB dB dB
Return Loss		DC - 1.0 GHz DC - 2.0 GHz DC - 2.5 GHz DC - 3.0 GHz		24 20 19 17		dB dB dB dB
Input Power for 1 dB Compression	Vctl = 0/+3V Vctl = 0/+5V Vctl = 0/+8V	0.5 - 3.0 GHz	20 27 30	23 30 33		dBm dBm dBm
Input Third Order Intercept (Two-tone Input Power = +17 dBm Each Tone)	Vctl = 0/+3V Vctl = 0/+5V Vctl = 0/+8V	0.5 - 3.0 GHz		31 51 54		dBm dBm dBm
Switching Characteristics		DC - 3.0 GHz				
tRISE, tFALL (10/90% RF) tON, tOFF (50% CTL to 10/90% RF)				70 90		ns ns

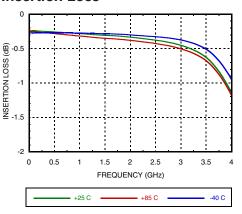


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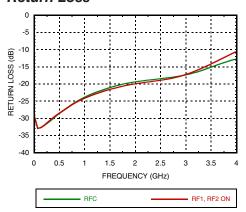
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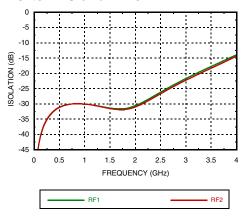
Insertion Loss



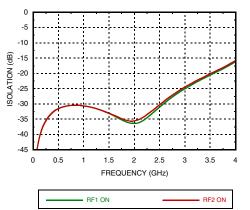
Return Loss



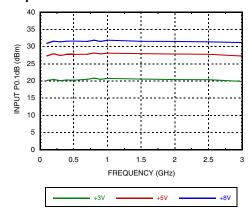
Isolation Between Ports RFC and RF1/RF2



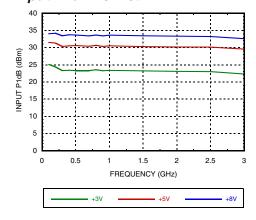
Isolation Between Ports RF1 and RF2



Input P0.1dB vs. Vctl



Input P1dB vs. Vctl



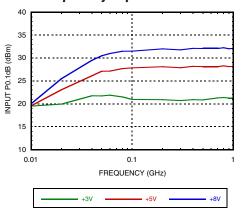


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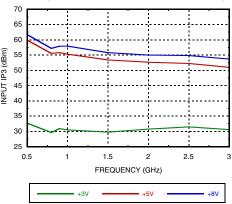




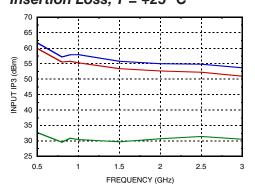
Low Frequency Input P0.1dB vs. Vctl



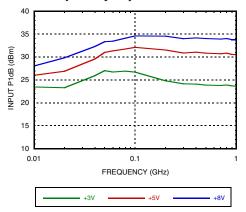
Input Third Order Intercept Point vs. Control Voltage



Insertion Loss, T = +25 °C



Low Frequency Input P1dB vs. Vctl



Absolute Maximum Ratings

•
+34 dBm
-0.2 to +12 Vdc
+32 dBm
150 °C
0.1 W
169°C/W
-65 to +150 °C
-40 to +85 °C
Class 1A

DC blocks are required at ports RFC, RF1 and RF2.



ELECTROSTATIC SENSITIVE DEVICE OBSERVE HANDLING PRECAUTIONS

Truth Table

Control Input		Control Current		
А	В	RFC to RF1	RFC to RF2	
Low	High	Off	On	
High	Low	On	Off	

Control Voltages

State	Bias Condition
Low	0 to 0.2 Vdc @ 1 μA Typical
High	+3 Vdc @ 0.5 μA Typical to +8 Vdc @ 14 μA Typical (±0.2 Vdc)

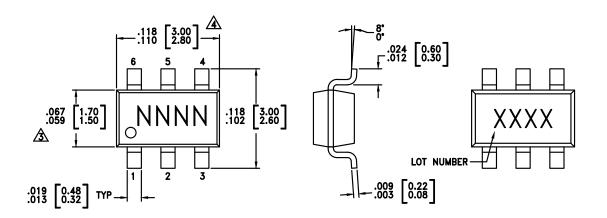


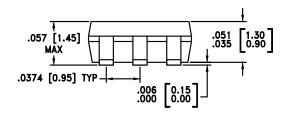
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Outline Drawing





NOTES:

- 1. LEADFRAME MATERIAL: COPPER ALLOY
- 2. DIMENSIONS ARE IN INCHES [MILLIMETERS].
- DIMENSION DOES NOT INCLUDE MOLDFLASH OF 0.15mm PER SIDE.
- DIMENSION DOES NOT INCLUDE MOLDFLASH OF 0.25mm PER SIDE.
- 5. ALL GROUND LEADS MUST BE SOLDERED TO PCB RF GROUND.

Package Information

Part Number	Package Body Material	Lead Finish	MSL Rating	Package Marking
HMC545A	Low Stress Injection Molded Plastic	Sn/Pb Solder	MSL1 [1]	H545A
HMC545AE	RoHS-compliant Low Stress Injection Molded Plastic	100% matte Sn	MSL1 [2]	545AE

^[1] Max peak reflow temperature of 235 $^{\circ}\text{C}$

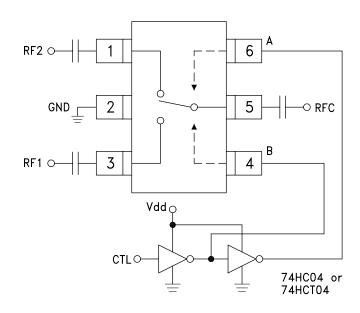
^[2] Max peak reflow temperature of 260 °C





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Typical Application Circuit



Notes:

- 1. Set logic gate Vdd = +3V to +5V and use HCT series logic to provide a TTL driver interface.
- 2. Control inputs A/B can be driven directly with CMOS logic (HC) with Vdd of +3V to +8V applied to the CMOS logic gates.
- 3. DC Blocking capacitors are required for each RF port as shown. Capacitor value determines lowest frequency of operation.
- 4. Highest RF signal power capability is achieved with Vdd = +8V and A/B set to 0/+8V.

Pin Descriptions

Pin Number	Function	Description	Interface Schematic
1, 3, 5	RF2, RF1, RFC	These pins are DC coupled and matched to 50 Ohms. Blocking capacitors are required.	
2	GND	This pin must be connected to RF/DC ground.	GND =
4	В	See truth and control voltage tables.	R
6	А	See truth and control voltage tables.	= c